

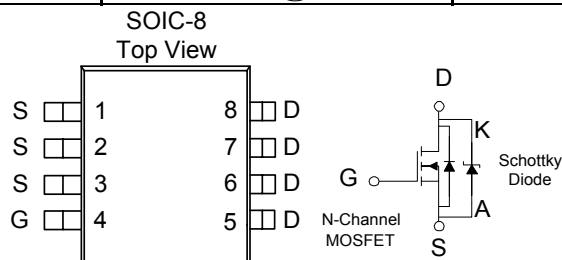
N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology

MOSFET PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
30	13.5 @ $V_{GS} = 10V$	13
	20 @ $V_{GS} = 4.5V$	11

SCHOTTKY PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_F (A)
30	0.61 V @ 3.0A	3.0



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^a	$T_A = 25^\circ C$	± 13	A
	$T_A = 70^\circ C$	± 11	
Pulsed Drain Current ^b	I_{DM}	± 50	
Continuous Source Current (Diode Conduction) ^a	I_S	2.3	A
Power Dissipation ^a	$T_A = 25^\circ C$	3.1	W
	$T_A = 70^\circ C$	2.2	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ C$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Case ^a	$R_{\theta JC}$	25	$^\circ C/W$
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	50	$^\circ C/W$

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1	μA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55°C			25	
On-State Drain Current ^A	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	20			A
Drain-Source On-Resistance ^A	r _{DS(on)}	V _{GS} = 10 V, I _D = 10 A			13.5	mΩ
		V _{GS} = 4.5 V, I _D = 8 A			18	
Forward Transconductance ^A	g _s	V _{DS} = 15 V, I _D = 10 A		40		S
Diode Forward Voltage	V _{SD}	I _S = 2.3 A, V _{GS} = 0 V		0.7		V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 10 A		12.5		nC
Gate-Source Charge	Q _{gs}			2.6		
Gate-Drain Charge	Q _{gd}			4.6		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 25 V, R _L = 25 Ω, I _D = 1 A, V _{GEN} = 10 V		20		nS
Rise Time	t _r			9		
Turn-Off Delay Time	t _{d(off)}			70		
Fall-Time	t _f			20		
Drain-Source Diode Characteristics and Maximum Ratings						
Maximum Continuous Drain-Source Diode Forward Current	I _S				3.0	A
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 3.0 A ^A		0.61		V

Notes

- a. Pulse test: PW ≤ 300us duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics (N-Channel)

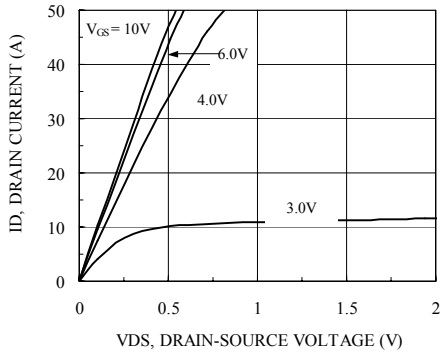


Figure 1. On-Region Characteristics

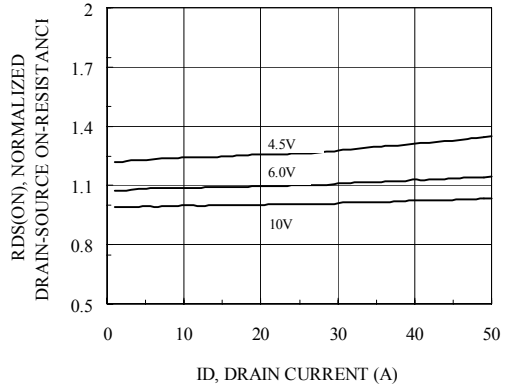


Figure 2. On-Resistance with Drain Current

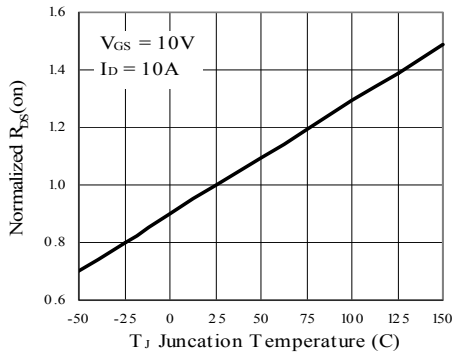


Figure 3. On-Resistance Variation with Temperature

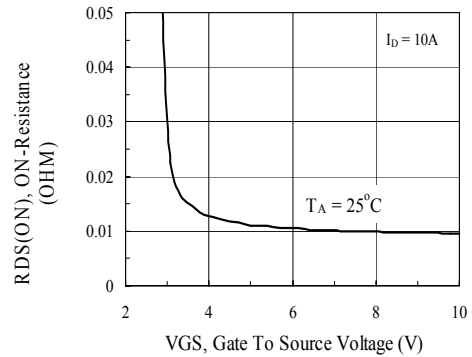


Figure 4. On-Resistance Variation with Gate to Source Voltage

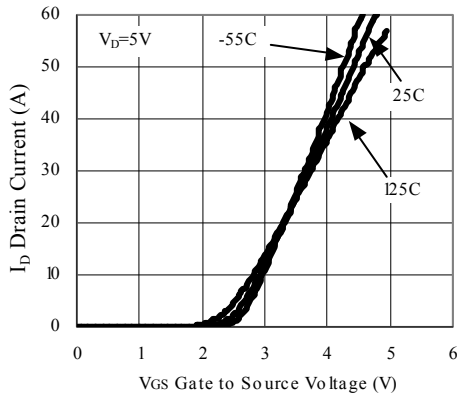


Figure 5. Transfer Characteristics

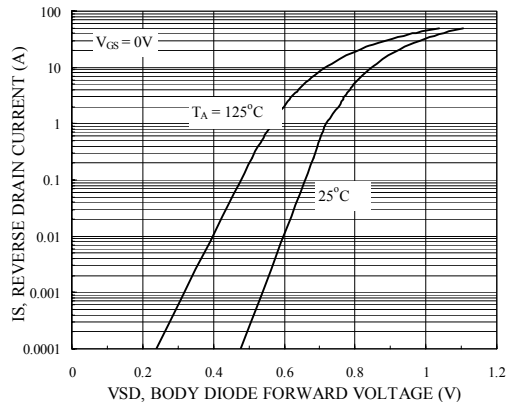


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics (N-Channel)

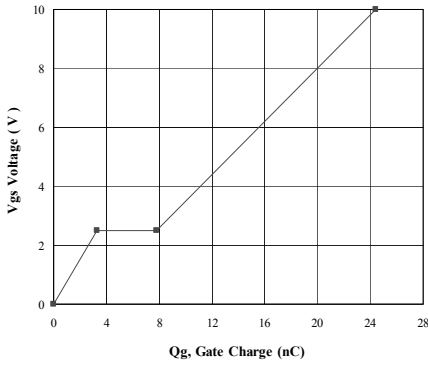


Figure 7. Gate Charge Characteristics

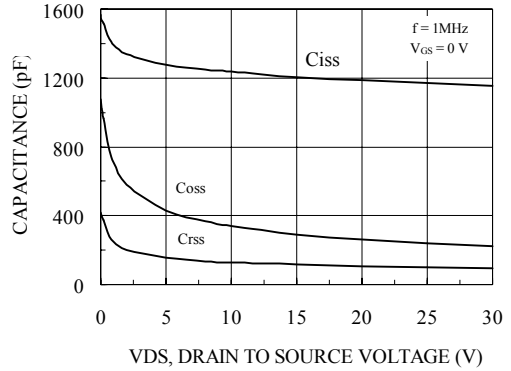


Figure 8. Capacitance Characteristics

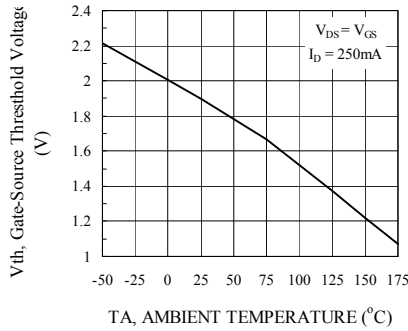


Figure 9. Threshold Vs Ambient Temperature

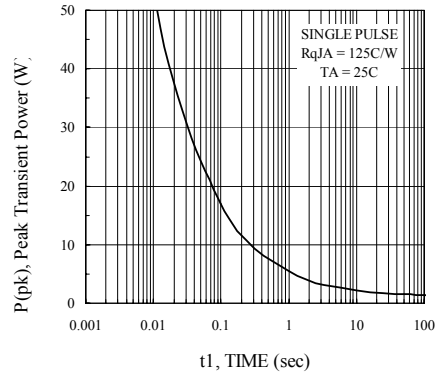


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

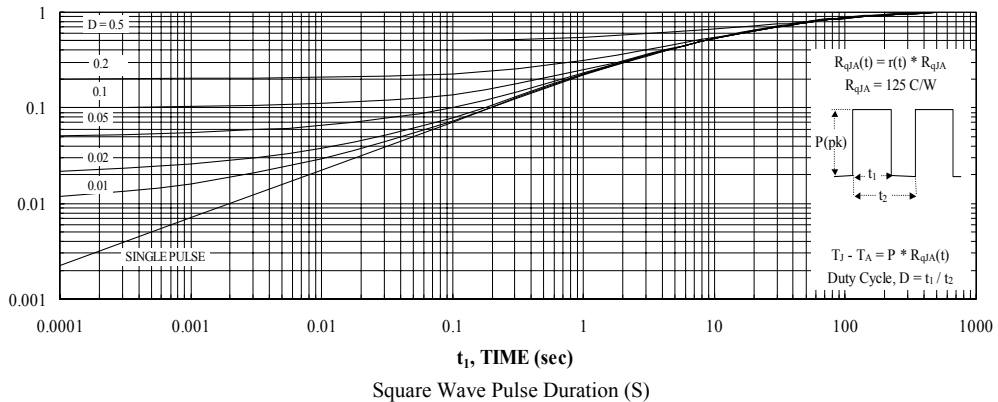
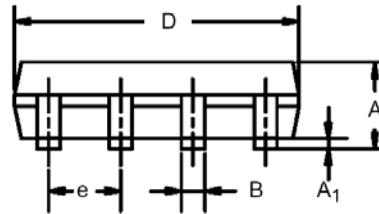
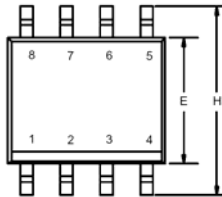


Figure 11. Transient Thermal Response Curve

Package Information

SO-8: 8LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

